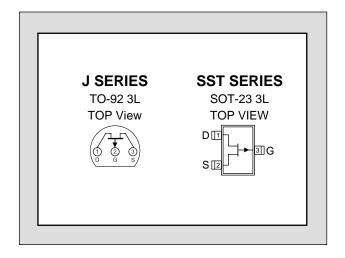


Improved Standard Products®

J/SST174 SERIES

SINGLE P-CHANNEL JFET SWITCH

FEATURES							
Replacement For SILICONIX J/SST174 SERIES							
LOW ON RESISTANCE $r_{DS(on)} \le 85\Omega$							
LOW GATE OPERATING CURRENT	$I_{D(off)} = 10pA$						
ABSOLUTE MAXIMUM RATINGS ¹							
@ 25 °C (unless otherwise stated)	@ 25 °C (unless otherwise stated)						
Maximum Temperatures							
Storage Temperature -55 to 150°C							
Junction Operating Temperature	-55 to 135°C						
Maximum Power Dissipation							
Continuous Power Dissipation ³	350mW						
Maximum Currents							
Gate Current I _G = -50mA							
Maximum Voltages							
Gate to Drain Voltage V _{GDS} = 30V							
Gate to Source Voltage V _{GSS} = 30V							



COMMON ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
BV _{GSS}	Gate to Source Breakdown Voltage	30			V	$I_G = 1\mu A$, $V_{DS} = 0V$
$V_{GS(F)}$	Gate to Source Forward Voltage		-0.7		V	$I_G = -1 \text{mA}, V_{DS} = 0 \text{V}$
Igss	Gate Reverse Current		0.01	1		$V_{GS} = 20V$, $V_{DS} = 0V$
IG	Gate Operating Current		0.01		nA	$V_{DG} = -15V, I_{D} = -1mA$
I _{D(off)}	Drain Cutoff Current		-0.01	-1		V _{DS} = -15V, V _{GS} = 10V

SPECIFIC ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	J/SST174		J/SST175		J/SST176		J/SST177		UNITS	CONDITIONS
STIVIBUL	CHARACTERISTIC	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	CONDITIONS
V _{GS(off)}	Gate to Source Cutoff Voltage	5	10	3	6	1	4	0.8	2.25	V	V _{DS} = -15V, I _D = -10nA
I _{DSS}	Drain to Source Saturation Current	-20	-195	-7	-90	-2	-55	-1.5	-30	mA	V _{DS} = -15V, V _{GS} = 0V
r _{DS(on)}	Drain to Source On Resistance		85		125		250		300	Ω	V _G S = 0V, V _D S = -0.1V

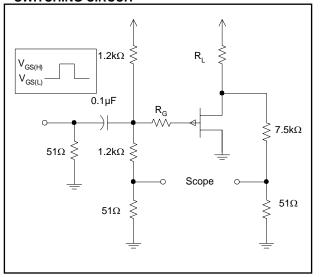
SWITCHING CHARACTERISTICS

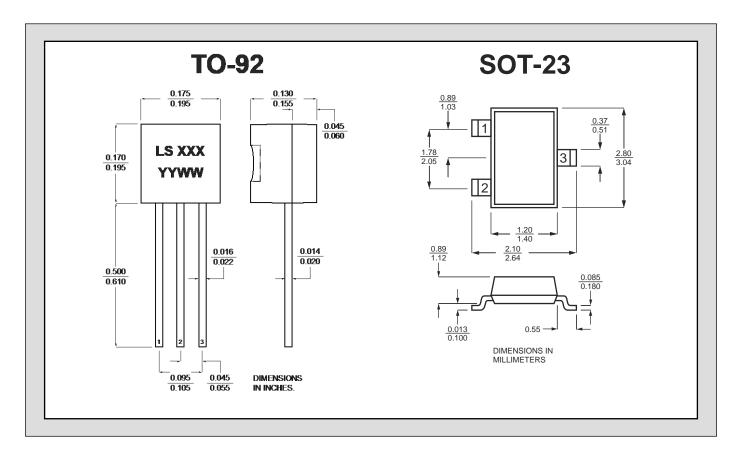
SYMBOL	CHARACTERISTIC	TYP	UNITS	CONDITIONS	
t _{d(on)}	Turn On Time	10	ns	$V_{GS(L)} = 0V$ $V_{GS(H)} = 10V$ See Switching	
tr	Turn On Rise Time	15			
t _{d(off)}	Turn Off Time	10			
t _f	Turn Off Fall Time	20		Circuit	

SWITCHING CIRCUIT PARAMETERS

	J/SST174	J/SST175	J/SST176	J/SST177
V_{DD}	-10V	-6V	-6V	-6V
V_{GG}	20V	12V	8V	5V
RL	560Ω	750Ω	1800Ω	5600Ω
Rg	100Ω	220Ω	390Ω	390Ω
I _{D(on)}	-15mA	-7mA	-3mA	-1mA

SWITCHING CIRCUIT





NOTES

- 1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
- Pulsed test: P_W ≤ 300µS Duty Cycle: 3%

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3. Derate 2.8mW/°C above 25 °C.